

1MBI1200UE-330

IGBT Modules

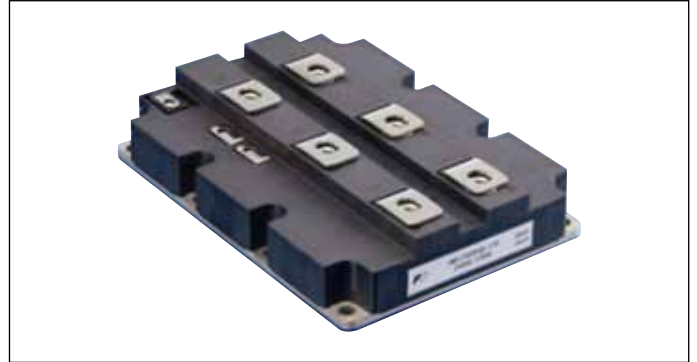
IGBT MODULE (U series) 3300V / 1200A / 1 in one package

■ Features

- AlSiC Baseplate
- AlN DCB substrate
- CTI ≥ 600
- V_{iso} 6000 Vac
- Low Inductance module structure

■ Applications

- Traction drives
- Industrial motor drives
- Wind power
- Chopper



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units	
Collector-Emitter voltage	V _{CES}		3300	V	
Gate-Emitter voltage	V _{GES}		±20	V	
Collector current	I _c	Continuous	T _c =25°C	2000	A
			T _c =80°C	1200	
	I _{c pulse}	1ms	T _c =25°C	4000	
			T _c =80°C	2400	
	-I _c			1200	
-I _{c pulse}	1ms		2400		
Collector power dissipation	P _c	1 device	14.7	kW	
Junction temperature	T _j		150	°C	
Storage temperature	T _{stg}		-40 ~ +125		
Isolation voltage	V _{iso}	AC : 1min.	6.0	kVAC	
Partial discharge extinction voltage	V _e	AC, Q≤10pC (acc. To IEC 1287)	2.6	kVAC	
Screw torque (*2)	Mounting		5.75	N·m	
	Main Terminals		10		
	Sense Terminals		2.5		

Note *1: All terminals should be connected together when isolation test will be done.

Note *2: Recommendable value : Mounting : 4.25-5.75 N·m (M6), Main Terminal : 8-10 N·m (M8), Sense Terminal : 1.7-2.5 N·m (M4)

● Electrical characteristics (at T_j = 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	I _{CES}	V _{GE} = 0V, V _{CE} = 3300V	-	-	1.0	mA	
Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V, V _{GE} = ±20V	-	-	4800	nA	
Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} = 20V, I _c = 1200mA	6.0	6.75	7.5	V	
Collector-Emitter saturation voltage	V _{CE(sat)} (main terminal)	V _{GE} = 15V I _c = 1200A	T _j = 25°C	-	2.43	2.66	V
			T _j = 125°C	-	3.15	3.45	
	V _{CE(sat)} (chip)		T _j = 25°C	-	2.28	2.51	
			T _j = 125°C	-	3.00	3.30	
Input capacitance	C _{ies}	V _{GE} = 0V, V _{CE} = 10V, f = 1MHz	-	240	-	nF	
Turn-on time	t _{on}	V _{CC} = 1800V, I _c = 1200A V _{GE} = ±15V, T _j = 125°C R _g = 1.6Ω	-	3.40	-	μs	
	t _r		-	2.30	-		
Turn-off time	t _{off}		-	2.40	-		
	t _r		-	0.40	-		
Forward on voltage	V _F (main terminal)	V _{GE} = 0V I _F = 1200A	T _j = 25°C	-	2.73	2.96	V
			T _j = 125°C	-	2.95	3.25	
	V _F (chip)		T _j = 25°C	-	2.58	2.81	
			T _j = 125°C	-	2.80	3.10	
Reverse recovery time	t _{rr}	I _F = 1200A	-	0.85	-	μs	
Lead resistance, terminal-chip	R lead		-	0.124	-	mΩ	

● Thermal resistance characteristics

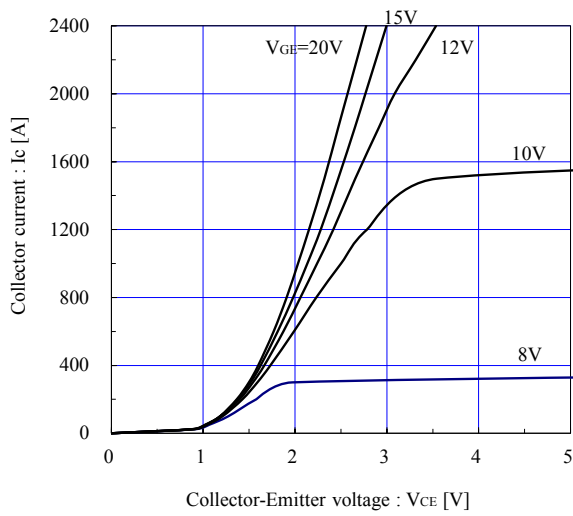
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R _{th(j-c)}	IGBT	-	-	8.5	°C/kW
		FWD	-	-	17.0	
Contact thermal resistance (1device)	R _{th(c-f)}	with Thermal Compound (*3)	-	4.0	-	

Note *3: This is the value which is defined mounting on the additional cooling fin with thermal compound.

Characteristics (Representative)

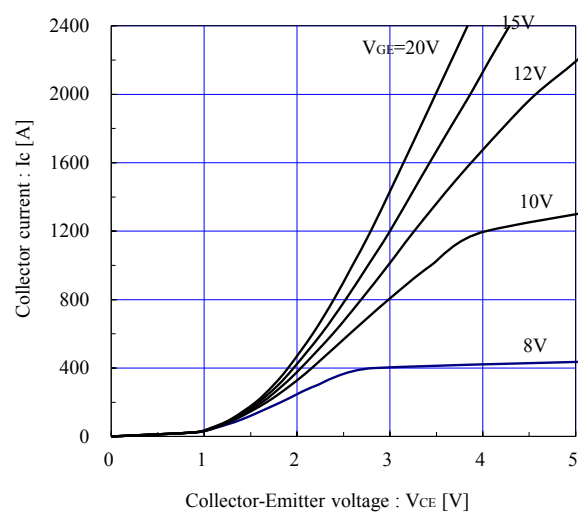
Collector current vs. Collector-Emitter voltage (typ.)

$T_j = 25^\circ\text{C}$ / chip



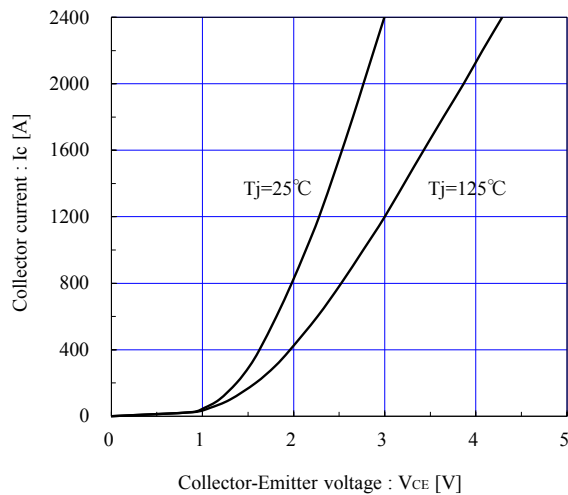
Collector current vs. Collector-Emitter voltage (typ.)

$T_j = 125^\circ\text{C}$ / chip



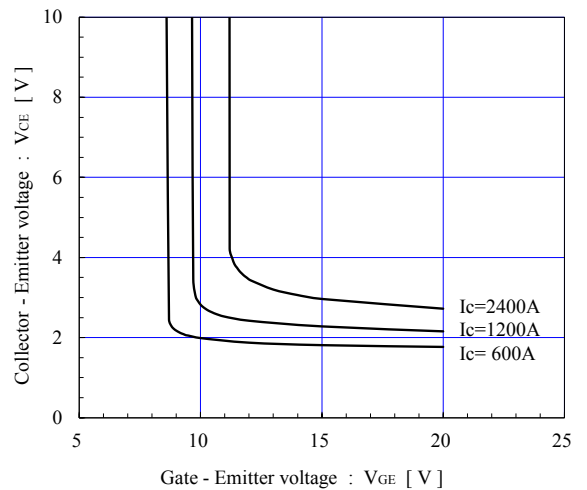
Collector current vs. Collector-Emitter voltage (typ.)

$V_{GE} = 15\text{V}$ / chip



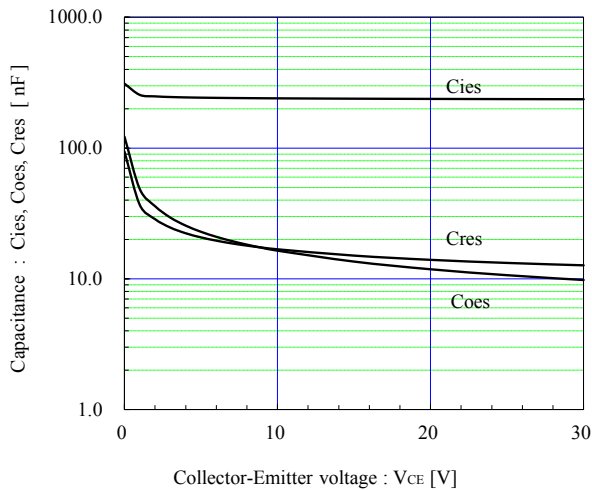
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)

$T_j = 25^\circ\text{C}$ / chip



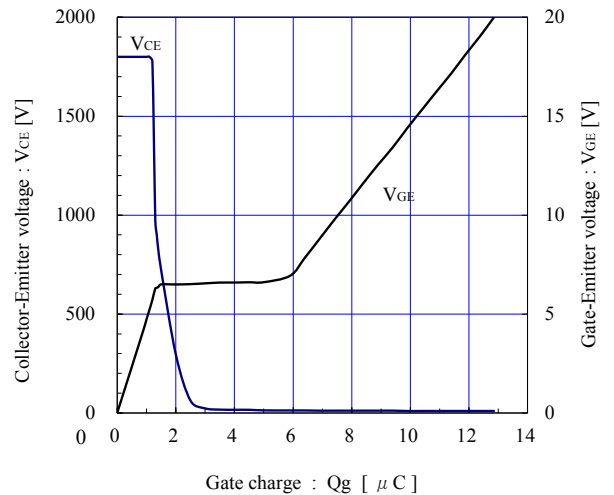
Capacitance vs. Collector-Emitter voltage (typ.)

$V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_j = 25^\circ\text{C}$



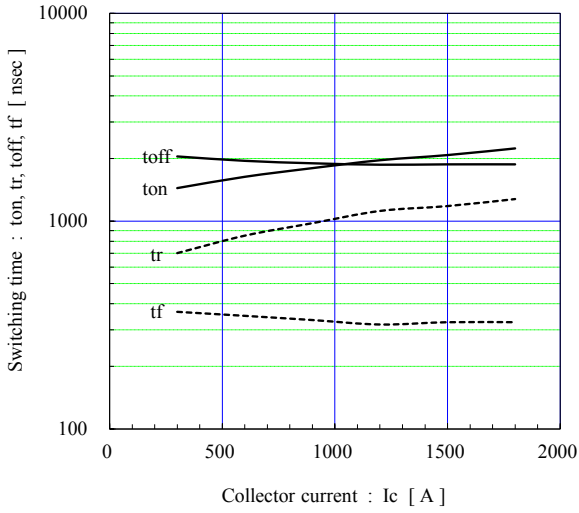
Dynamic Gate charge (typ.)

$V_{CC} = 1800\text{V}$, $T_j = 25^\circ\text{C}$



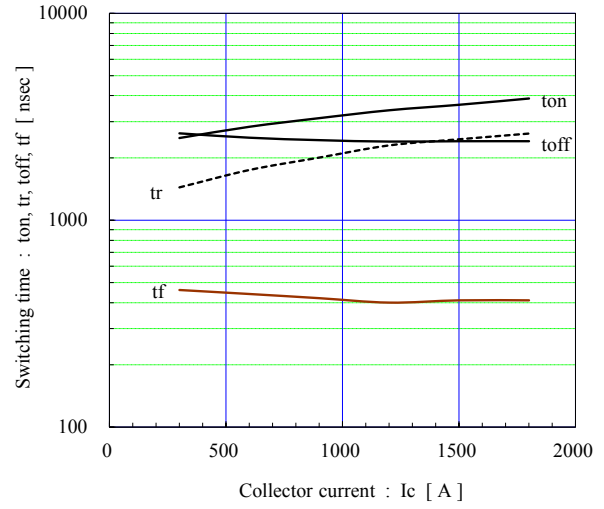
Switching time vs. Collector current (typ.)

$V_{cc}=1800V, V_{GE}=\pm 15V, R_g=1.6\Omega, T_j=25^\circ C$



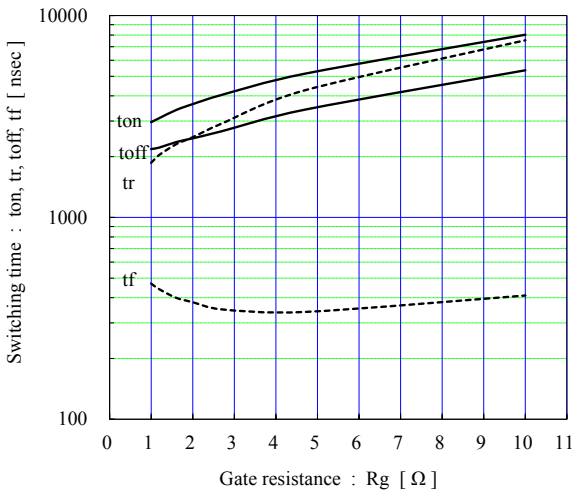
Switching time vs. Collector current (typ.)

$V_{cc}=1800V, V_{GE}=\pm 15V, R_g=1.6\Omega, T_j=125^\circ C$



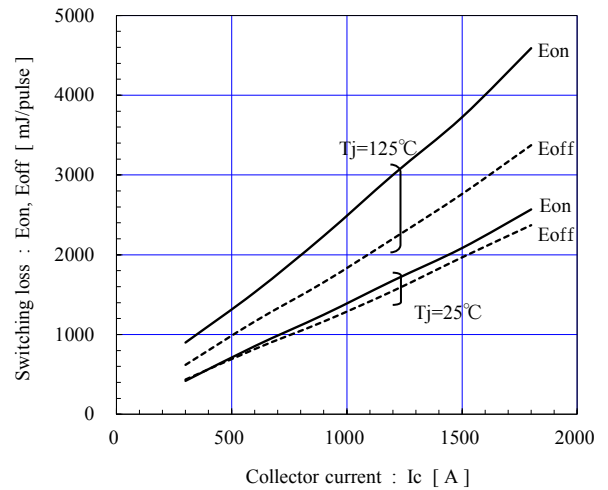
Switching time vs. Gate resistance (typ.)

$V_{cc}=1800V, I_c=1200A, V_{GE}=\pm 15V, T_j=125^\circ C$



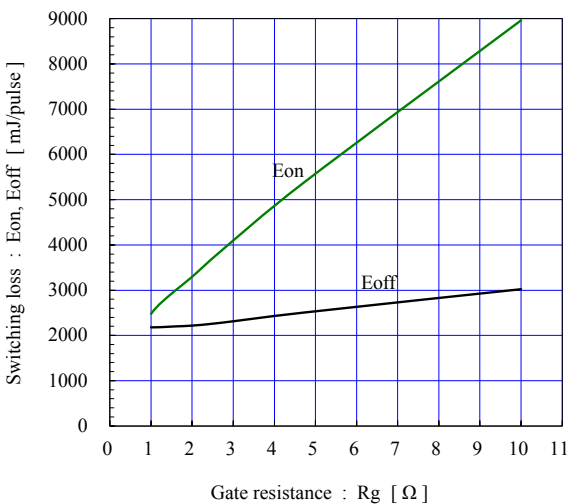
Switching loss vs. Collector current (typ.)

$V_{cc}=1800V, V_{GE}=\pm 15V, R_g=1.6\Omega$



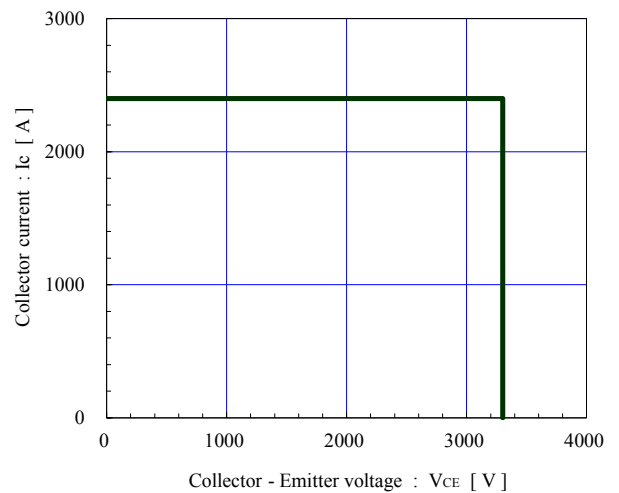
Switching loss vs. Gate resistance (typ.)

$V_{cc}=1800V, I_c=1200A, V_{GE}=\pm 15V, T_j=125^\circ C$

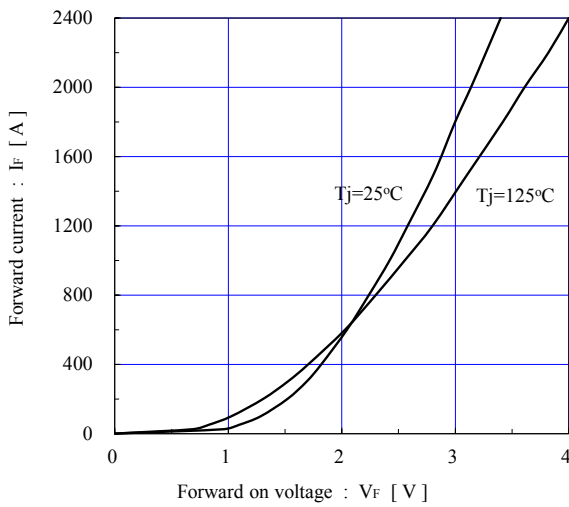


Reverse bias safe operating area (max.)

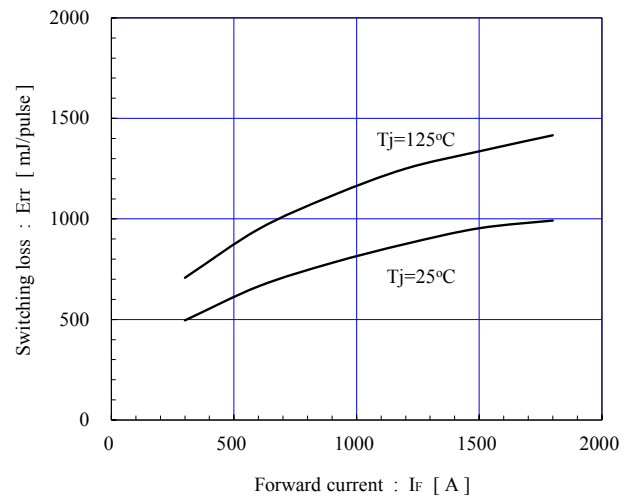
$\pm V_{GE}=15V, T_j=125^\circ C / \text{chip}$



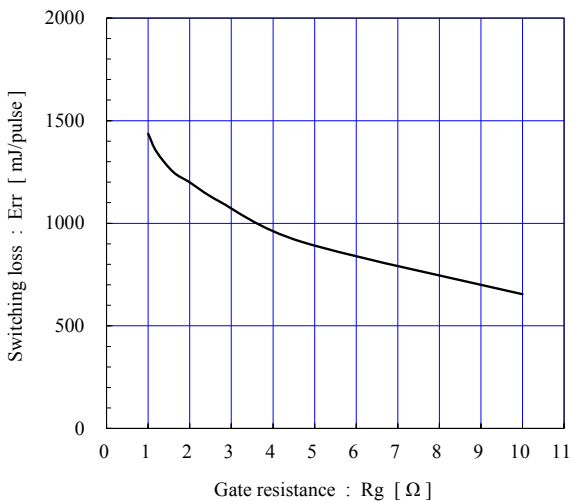
Forward current vs. Forward on voltage (typ.)
chip



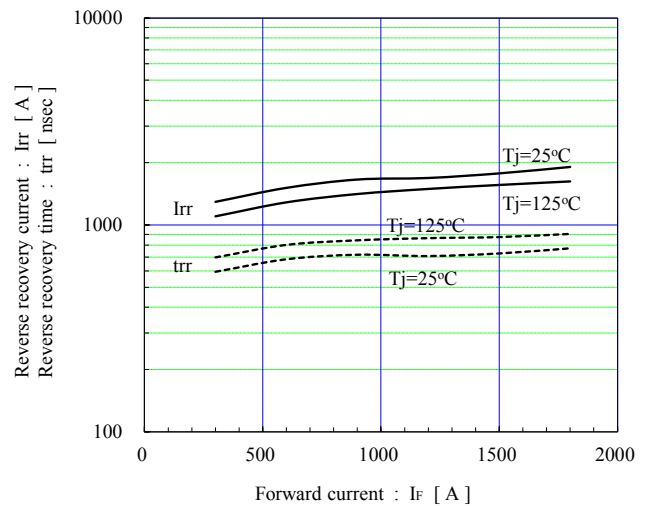
Switching loss vs. Collector current (typ.)
 $V_{cc}=1800\text{V}$, $V_{GE}=\pm 15\text{V}$, $R_g=1.6\Omega$



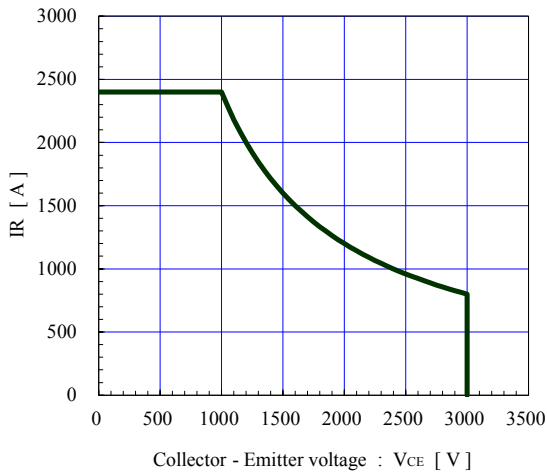
Switching loss vs. Gate resistance (typ.)
 $V_{cc}=1800\text{V}$, $I_f=1200\text{A}$, $V_{GE}=\pm 15\text{V}$, $T_j=125^\circ\text{C}$



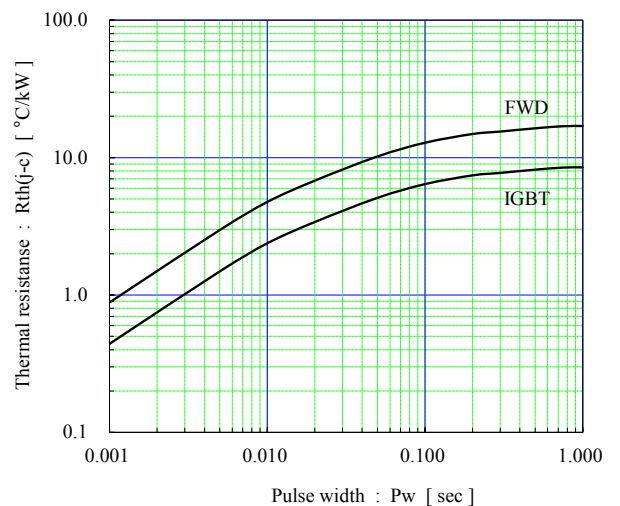
Reverse recovery characteristics (typ.)
 $V_{cc}=1800\text{V}$, $V_{GE}=\pm 15\text{V}$, $R_g=1.6\Omega$



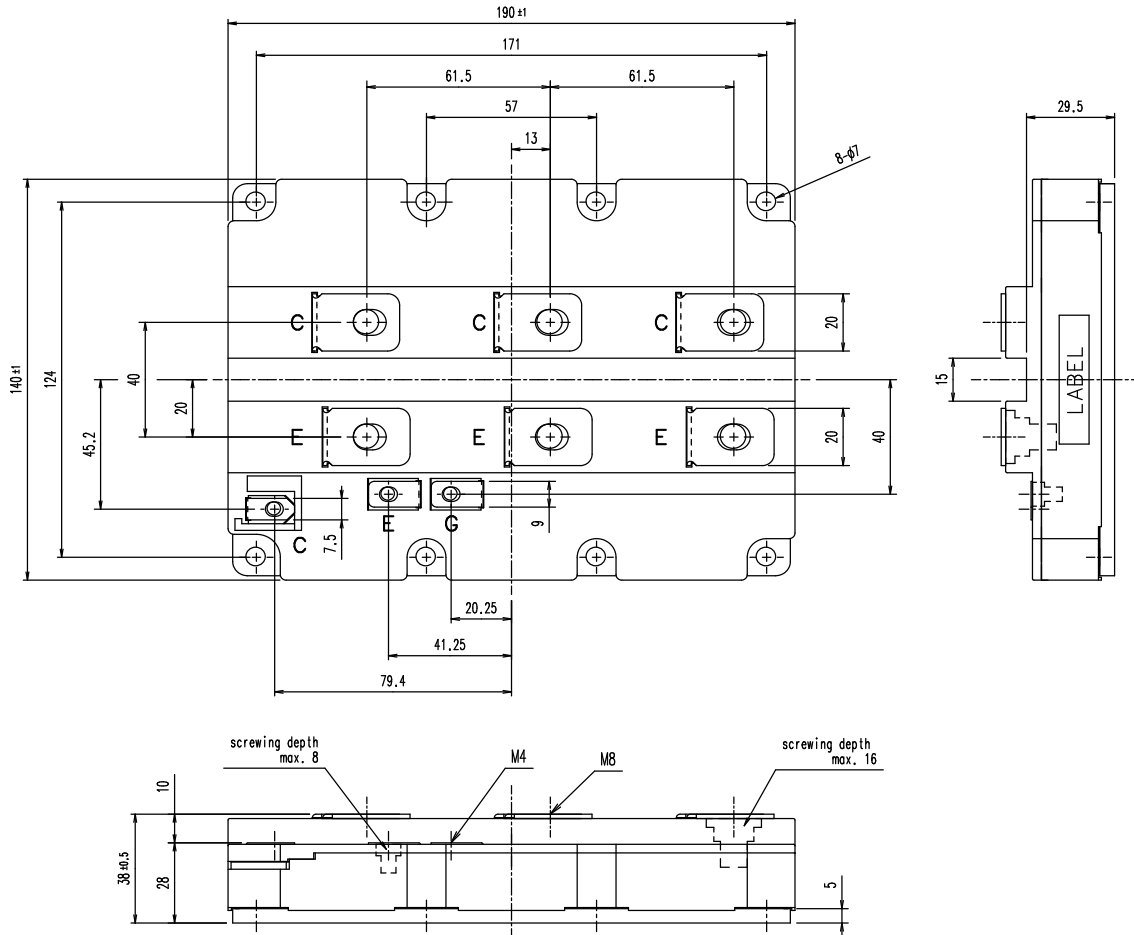
FWD safe operating area (max.)
 $T_j=125^\circ\text{C}$



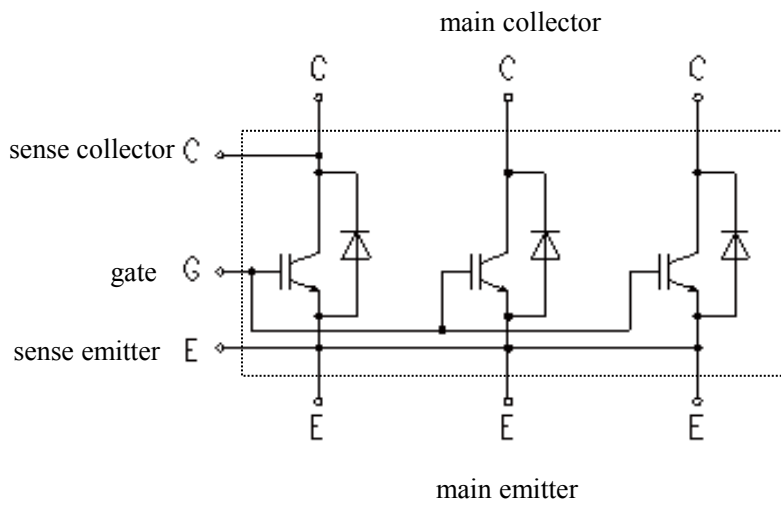
Transient thermal resistance (max.)



■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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